SPICE Model Parameters

Please copy this code from the SPICE model into LTSPICE (version 4) software for simulation of the GB05SHT12-CAL.

```
*       MODEL OF GeneSiC Semiconductor Inc.
*
*       $Revision:   1.0            $
*       $Date:    05-SEP-2013        $
*
*       GeneSiC Semiconductor Inc.
*       43670 Trade Center Place Ste. 155
*       Dulles, VA 20166
*
*       COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
*       ALL RIGHTS RESERVED
*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of GB05SHT12-CAL SPICE Model
*
.SUBCKT GB05SHT12 ANODE KATHODE
R1 ANODE INT R=((TEMP-24)*0.0021); Temperature Dependant Resistor
D1 INT KATHODE GB05SHT12_25C; Call the 25C Diode Model
D2 ANODE KATHODE GB05SHT12_PIN; Call the PiN Diode Model
.MODEL GB05SHT12_25C D
+ IS       4.45E-15       RS       0.206
+ N        1.18144        IKF      112.92
+ EG       1.2            XTI      3
+ CJO      3.00E-10       VJ       0.419
+ M        1.6            FC       0.5
+ TT       1.00E-10       BV       1200
+ IBV      1.00E-03       VPK      1200
+ IAVE     5              TYPE     SiC_Schottky
+ MFG      GeneSiC_Semiconductor
.MODEL GB05SHT12_PIN D
+ IS       2.93E-12       RS       0.35326
+ N        4.6113         IKF      0.0043236
+ EG       3.23           XTI      60
+ FC       0.5            TT       0
+ BV       1200           IBV      1.00E-03
+ VPK      1200           IAVE     2.5
+ TYPE     SiC_PiN
.ENDS
*
* End of GB05SHT12-CAL SPICE Model
```